

HD74LV125A

Quad. Bus Buffer Gates with 3-state Outputs

REJ03D0315-0300Z (Previous ADE-205-245A (Z)) Rev.3.00 Jun. 03, 2004

Description

The HD74LV125A features independent line drivers with three state outputs. Each output is disabled when the associated output enable (\overline{OE}) input is high. To ensure the high impedance state during power up or power down, \overline{OE} should be connected to V_{CC} through a pull-down resistor; the minimum value of the resistor is determined by the current souring capability of the driver. Low-voltage and high-speed operation is suitable for the battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

Features

- $V_{CC} = 2.0 \text{ V to } 5.5 \text{ V operation}$
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@ $V_{CC} = 0$ V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.3 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Output current ± 8 mA (@V_{CC} = 3.0 V to 3.6 V), ± 16 mA (@V_{CC} = 4.5 V to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV125AFPEL	SOP-14 pin(JEITA)	FP-14DAV	FP	EL (2,000 pcs/reel)
HD74LV125ARPEL	SOP-14 pin(JEDEC)	FP-14DNV	RP	EL (2,500 pcs/reel)
HD74LV125ATELL	TSSOP-14 pin	TTP-14DV	Т	ELL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

Function Table

Inputs

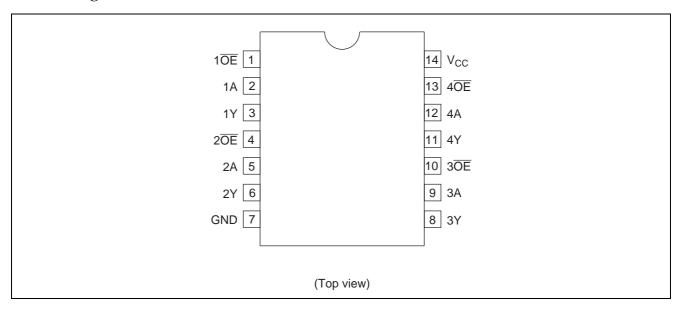
ŌĒ	A	Output Y
L	Н	Н
L	L	L
Н	X	Z

Note: H: High level L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	-0.5 to 7.0	V	
Input voltage range*1	Vı	-0.5 to 7.0	V	
Output voltage range*1,2	Vo	-0.5 to V _{CC} + 0.5	V	Output: H or L
		-0.5 to 7.0		V _{CC} : OFF or Output: Z
Input clamp current	I _{IK}	-20	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	±35	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±70	mA	
Maximum power dissipation at	P _T	785	mW	SOP
Ta = 25°C (in still air)*3		500		TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

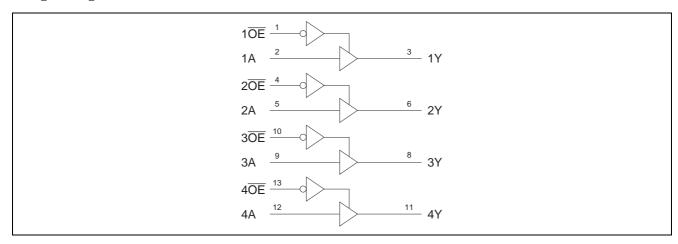
- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	Vcc	2.0	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	H or L
		0	5.5		High impedance state
Output current	I _{OH}	_	-50	μΑ	V _{CC} = 2.0 V
		_	-2	mA	V _{CC} = 2.3 to 2.7 V
		_	-8		V _{CC} = 3.0 to 3.6 V
		_	-16		V _{CC} = 4.5 to 5.5 V
	I _{OL}	_	50	μΑ	V _{CC} = 2.0 V
		_	2	mA	V _{CC} = 2.3 to 2.7 V
		_	8		V _{CC} = 3.0 to 3.6 V
		_	16		V _{CC} = 4.5 to 5.5 V
Input transition rise or fall rate	Δt /Δν	0	200	ns/V	V _{CC} = 2.3 to 2.7 V
		0	100		V _{CC} = 3.0 to 3.6 V
		0	20		V _{CC} = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Logic Diagram



DC Electrical Characteristics

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$

Item	Symbol	V _{CC} (V)*	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.0	1.5	_	_	V	
		2.3 to 2.7	$V_{CC} \times 0.7$	_	_		
		3.0 to 3.6	$V_{CC} \times 0.7$	_	_		
		4.5 to 5.5	$V_{CC} \times 0.7$	_	_		
	V _{IL}	2.0	_	_	0.5		
		2.3 to 2.7	_	_	$V_{CC} \times 0.3$		
		3.0 to 3.6	_	_	$V_{CC} \times 0.3$		
		4.5 to 5.5	_	_	$V_{CC} \times 0.3$		
Output voltage	V_{OH}	Min to Max	V _{CC} – 0.1	_	_	V	I _{OH} = -50 μA
		2.3	2.0	_	_		$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_		$I_{OH} = -8 \text{ mA}$
		4.5	3.8	_	_		$I_{OH} = -16 \text{ mA}$
	V_{OL}	Min to Max	_	_	0.1		$I_{OL} = 50 \mu\text{A}$
		2.3	_	_	0.4		$I_{OL} = 2 \text{ mA}$
		3.0	_	_	0.44		$I_{OL} = 8 \text{ mA}$
		4.5	_	_	0.55		$I_{OL} = 16 \text{ mA}$
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	$V_I = 5.5 \text{ V or GND}$
Off-state output current	l _{OZ}	5.5	_	_	±5	μΑ	$V_O = V_{CC}$ or GND
Quiescent supply	I _{CC}	5.5	_	_	20	μΑ	$V_I = V_{CC}$ or GND, $I_O = 0$
current							
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V_1 or $V_0 = 0$ V to 5.5 V
Input capacitance	C _{IN}	3.3	_	3.0	_	pF	$V_I = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $V_{CC}=2.5\pm0.2~V$

		Ta =	25°C		Ta = -4	0 to 85°C		Test	FROM	то
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	6.8	13.0	1.0	15.5	ns	C _L = 15 pF	Α	Υ
delay time	t_{PHL}	_	8.7	16.5	1.0	18.5	_	C _L = 50 pF		
Enable time	t _{ZH}	_	7.0	13.0	1.0	15.5	ns	$C_L = 15 pF$	ŌĒ	Υ
	t_{ZL}	_	8.8	16.5	1.0	18.5	_	C _L = 50 pF		
Disable time	t _{HZ}	_	5.1	14.7	1.0	17.0	ns	$C_L = 15 pF$	ŌĒ	Υ
	t_{LZ}	_	7.3	18.2	1.0	20.5	_	C _L = 50 pF	_	

 $V_{CC} = 3.3 \pm 0.3 \ V$

		Ta =	25°C		Ta = -4	10 to 85°C		Test	FROM	то
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	4.8	8.0	1.0	9.5	ns	C _L = 15 pF	Α	Υ
delay time	t _{PHL}	_	6.1	11.5	1.0	13.0		C _L = 50 pF	<u></u>	
Enable time	t _{zH}	_	4.8	8.0	1.0	9.5	ns	C _L = 15 pF	ŌĒ	Υ
	t_{ZL}	_	6.2	11.5	1.0	13.0	_	C _L = 50 pF		
Disable time	t _{HZ}	_	4.1	9.7	1.0	11.5	ns	C _L = 15 pF	ŌĒ	Υ
	t_{LZ}	_	5.5	13.2	1.0	15.0		C _L = 50 pF		

 $V_{CC} = 5.0 \pm 0.5 \text{ V}$

		Ta =	25°C		Ta = -4	40 to 85°C		Test	FROM	TO
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	3.4	5.5	1.0	6.5	ns	C _L = 15 pF	Α	Υ
delay time	t_{PHL}	_	4.3	7.5	1.0	8.5		C _L = 50 pF		
Enable time	t _{ZH}	_	3.4	5.1	1.0	6.0	ns	C _L = 15 pF	ŌĒ	Υ
	t_{ZL}	_	4.4	7.1	1.0	8.0	_	C _L = 50 pF		
Disable time	t _{HZ}	_	3.2	6.8	1.0	8.0	ns	C _L = 15 pF	ŌĒ	Y
	t_{LZ}	_	4.0	8.8	1.0	10.0	_	C _L = 50 pF	_	

Output-skew Characteristics

		$V_{CC} = (V)$	Ta = 25°	С	Ta = -40		
Item	Symbol		Min	Max	Min	Max	Unit
Output skew	t _{sk (O)}	2.3 to 2.7	_	2.0	_	2.0	ns
		3.0 to 3.6	_	1.5	_	1.5	<u></u>
		4.5 to 5.5		1.0	_	1.0	

Note: Skew between any outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

Operating Characteristics

 $C_L = 50 pF$

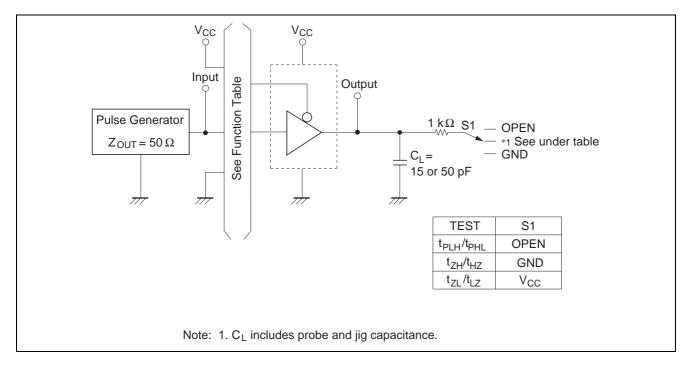
			1a = 2	5°C			
Item	Symbol	$V_{CC} = (V)$	Min	Тур	Max	Unit	Test Conditions
Power dissipation capacitance	C _{PD}	3.3	_	15.5	_	pF	f = 10 MHz
		5.0	_	17.6	_		

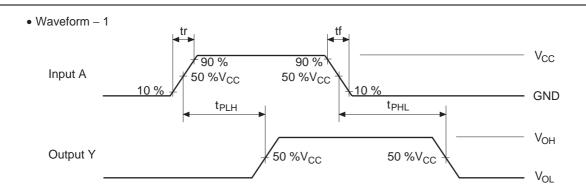
Noise Characteristics

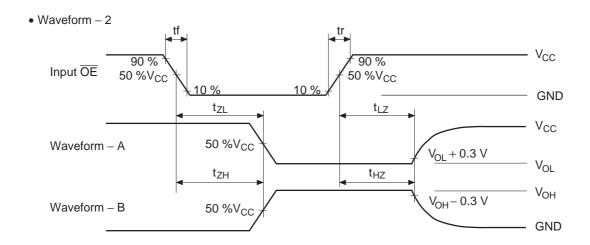
 $C_L = 50 pF$

			Ta = 25°C				
Item	Symbol	$V_{CC} = (V)$	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V _{OL}	V _{OL (P)}	3.3	_	0.3	0.8	V	
Quiet output, minimum dynamic V _{OL}	$V_{OL\ (V)}$	3.3	_	-0.3	-0.8	V	
Quiet output, minimum dynamic V _{OH}	V _{OH (V)}	3.3	_	3.0	_	V	
High-level dynamic input voltage	$V_{\text{IH (D)}}$	3.3	2.31	_	_	V	
Low-level dynamic input voltage	$V_{IL\;(D)}$	3.3	_	_	0.99	V	

Test Circuit



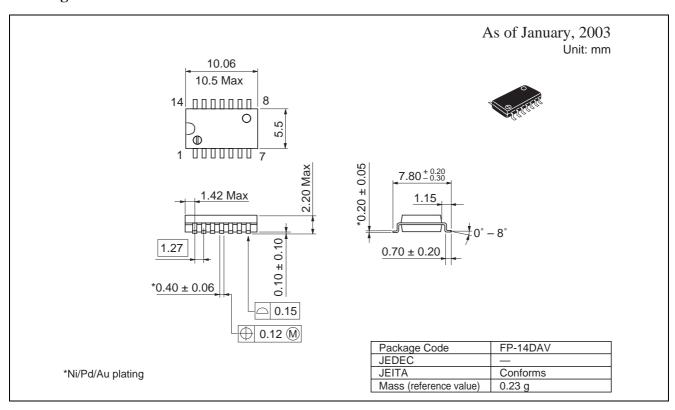


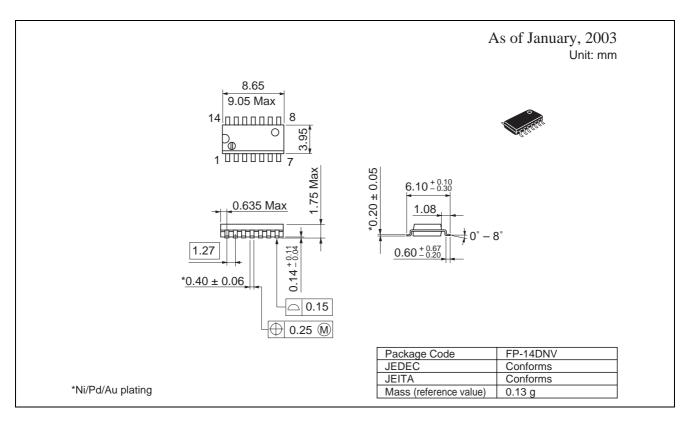


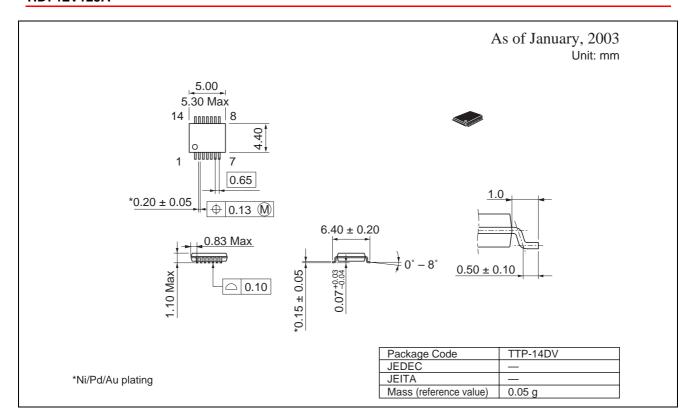
Notes: 1. $t_r \le 3$ ns, $t_f \le 3$ ns

- 2. Input waveform: PRR \leq 1 MHz, duty cycle 50%
- 3. Waveform–A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 4. Waveform—B is for an output with internal conditions such that the output is high except when disabled by the output control.

Package Dimensions







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